

Title (en)
DRAM CELL SYSTEM AND METHOD FOR PRODUCING SAME

Title (de)
DRAM-ZELLENANORDNUNG UND VERFAHREN ZU DEREN HERSTELLUNG

Title (fr)
CONFIGURATION DE CELLULE DRAM ET SON PROCEDE DE PRODUCTION

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Application
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Abstract (en)
[origin: DE19845004A1] The invention relates to a DRAM cell system and a method for the production thereof. The inventive DRAM cell system has folded-bit lines. Memory cells having a surface of 4F<2> can be produced and are arranged in columns and rows, and the bit-lines are parallel to the columns. Bit lines (7, 8) run parallel to the columns. First word lines (9, 10) contact every adjacent second contact structure (A) of a memory cell along a row. Second word lines (12,13) contact the remaining contact structures. Both word lines run parallel to the rows. One of the first word lines and one of the second word lines respectively overlap one of the rows. The word lines and bit lines are separated from each other by insulating layers (6, 11), insulations (I1, I2) and insulating spacers (Sp1, Sp2). Contacts for the word lines and bit lines are produced partly in a self-adjusting manner.

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